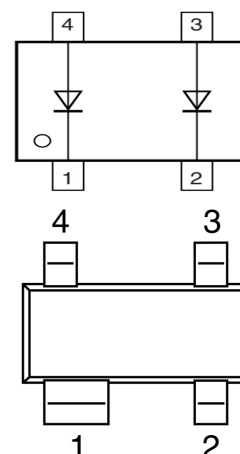


Silicon Epitaxial Planar Diodes

High voltage switching diode

Marking : KT8



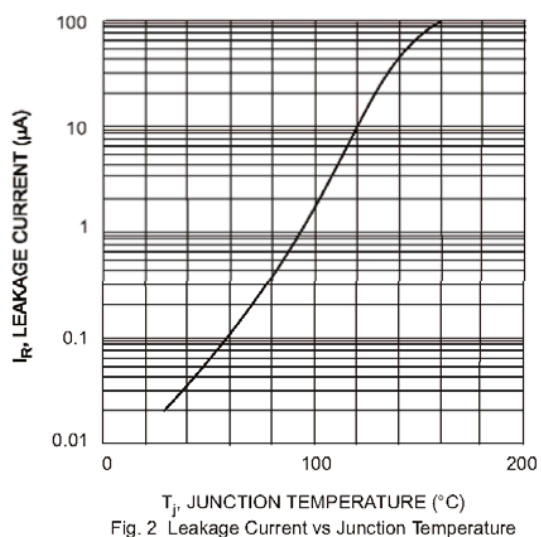
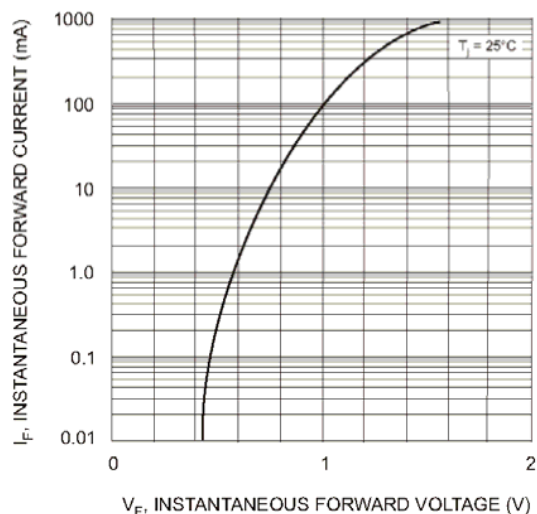
SOT143

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	250	V
Reverse Voltage	V_R	200	V
Forward Current	$I_{F(AV)}$	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1.7 3 9	A
		at $t = 10\text{ ms}$ at $t = 100\text{ }\mu\text{s}$ at $t = 1\text{ }\mu\text{s}$	
Power Dissipation	P_{tot}	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}$

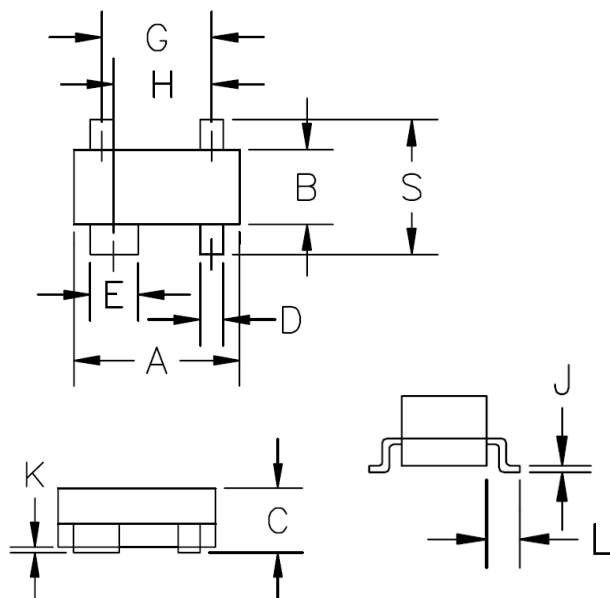
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	- -	1 1.25	V
Reverse Current at $V_R = 200\text{ V}, T_j = 25\text{ }^{\circ}\text{C}$ at $V_R = 200\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	I_R	- -	100 100	nA μA
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_{tot}	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns



Package Outline

Plastic surface mounted package

SOT-143



DIMENSIONS					
DIM ^N	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	—
B	.047	.055	1.20	1.40	—
C	.031	.047	.80	1.20	—
D	.014	.018	.37	.510	—
E	.030	.035	.76	.940	—
G	.076	BSC	1.92	BSC	—
H	.068	BSC	1.72	BSC	—
J	.003	.005	.085	.180	—
K	.002	.005	.013	0.10	—
L	.010	.022	—	.55	REF
S	.082	.104	2.10	2.64	—